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Crystallographic and optical properties of CuGa₃S₅, CuGa₃Se₅ and

CuIn₃(S, Se)₅ and CuGa₃(S, Se)₅ systems

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Abstract

To clarify the solid solution regions of $CuIn_3(S_xSe_{1-x})_5$ and $CuGa_3(S_xSe_{1-x})_5$ systems and their optical properties, we prepared CuIn₃(S,Se)₅ and CuGa₃(S,Se)₅ samples by a mechanochemical process and post-heating. Single-phase solid solutions with a tetragonal stannite-type structure could not be obtained for $CuIn_3(S_xSe_{1-x})_5$ with $0 \le x < 1$ 0.1. On the other hand, we successfully obtained single-phase solid solutions with a tetragonal stannite-type structure for $CuGa_3(S_xSe_{1-x})_5$ with $0.0 \le x \le 1.0$. The solid solution region of the CuGa₃(S_xSe_{1-x})₅ system is much wider than that of the $CuIn_3(S_xSe_{1-x})_5$ system. The band gap energy of the $CuGa_3(S_xSe_{1-x})_5$ solid solution linearly increased from 1.85 eV of CuGa₃Se₅ (x = 0.0) to 2.58 eV of CuGa₃S₅ (x = 1.0). The energy levels of the valence band maxima (VBMs) were estimated from the ionization energies measured by photoemission yield spectroscopy (PYS). The ionization energy of stannite-type CuGa₃Se₅ (5.69 eV) is approximately equal to that of CuIn₃Se₅ (5.65 eV). The energy levels of the VBMs of the CuGa₃(S_xSe_{1-x})₅ solid solution decrease with increasing S content, x=S/(Se+S) ratio. The conduction band minimum (CBM) levels of $CuGa_3(S_xSe_{1-x})_5$ are almost constant with x=S/(Se+S) ratio. CuIn₃Se₅, CuGa₃Se₅, CuGa₃S₅ and CuGa₃(S,Se)₅ solid solution are expected to be useful for controlling the valence band offset ($\Delta E_{\rm v}$) and the conduction band offset ($\Delta E_{\rm c}$) at the interface between buffer layer and absorber layer in CIGS solar cells.

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